

MOSFET

CoolSiC™ MOSFET 650 V G2

Built on Infineon's robust 2nd generation Silicon Carbide trench technology, the 650 V CoolSiC™ MOSFET delivers unparalleled performance, superior reliability, and great ease of use. It enables cost effective, highly efficient, and simplified designs to fulfill the ever-growing system and market needs.

Features

- Ultra-low switching losses
- Benchmark gate threshold voltage, $V_{GS(th)} = 4.5\text{ V}$
- Robust against parasitic turn-on even with 0 V turn-off gate voltage
- Flexible driving voltage and compatible with bipolar driving scheme
- Robust body diode operation under hard commutation events
- .XT interconnection technology for best-in-class thermal performance

Benefits

- Enables high efficiency and high power density designs
- Facilitates great ease of use and integration
- Provides the best price performance ratio compared to Industry's most ambitious roadmaps
- Reduces the size, weight and bill of materials of the systems
- Enhances system robustness and reliability

Potential applications

- SMPS
- Solar PV inverters
- Energy storage and battery formation
- UPS
- EV charging infrastructure
- Motor drives

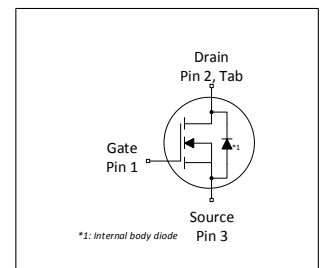
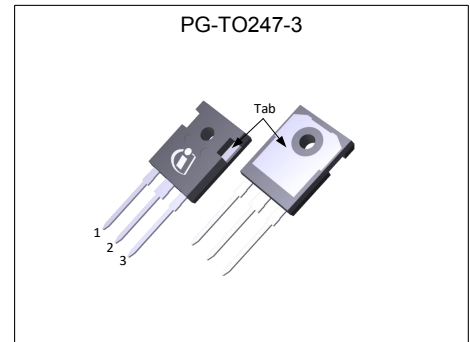
Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DSS} over full $T_{j,range}$	650	V
$R_{DS(on),typ}$	50	mΩ
$R_{DS(on),max}$	62	mΩ
$Q_{G,typ}$	22	nC
$I_{D,pulse}$	113	A
$Q_{oss} @ 400\text{ V}$	42	nC
$E_{oss} @ 400\text{ V}$	5.7	μJ

Type / Ordering Code	Package	Marking	Related Links
IMW65R050M2H	PG-TO247-3	65R050M2	see Appendix A



RoHS

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1 Maximum ratings

at $T_j = 25\text{ °C}$, unless otherwise specified.

Note: for optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous DC drain current ¹⁾	I_{DDC}	-	-	38 27	A	$T_C = 25\text{ °C}$ $T_C = 100\text{ °C}$
Peak drain current ²⁾	I_{DM}	-	-	113	A	$T_C = 25\text{ °C}$, $V_{GS} = 18\text{ V}$
Avalanche energy, single pulse	E_{AS}	-	-	105	mJ	$I_D = 3.9\text{ A}$, $V_{DD} = 50\text{ V}$; see table 11
Avalanche energy, repetitive	E_{AR}	-	-	0.52	mJ	$I_D = 3.9\text{ A}$, $V_{DD} = 50\text{ V}$; see table 11
Avalanche current, single pulse	I_{AS}	-	-	3.9	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	200	V/ns	$V_{DS} = 0...400\text{ V}$
Gate source voltage (static) ³⁾	V_{GS}	-7	-	23	V	-
Gate source voltage (transient)	V_{GS}	-10	-	25	V	$t_p \leq 500\text{ ns}$, duty cycle $\leq 1\%$
Power dissipation	P_{tot}	-	-	153	W	$T_C = 25\text{ °C}$
Storage temperature	T_{stg}	-55	-	150	°C	-
Operating junction temperature	T_j	-55	-	175	°C	-
Mounting torque	-	-	-	60	Ncm	M3 and M3.5 screws
Continuous reverse drain current ¹⁾	I_{SDC}	-	-	38 26.3	A	$V_{GS} = 18\text{ V}$, $T_C = 25\text{ °C}$ $V_{GS} = 0\text{ V}$, $T_C = 25\text{ °C}$
Peak reverse drain current ²⁾	I_{SM}	-	-	113 34	A	$T_C = 25\text{ °C}$, $t_p \leq 250\text{ ns}$ $T_C = 25\text{ °C}$
Insulation withstand voltage	V_{ISO}	-	-	n.a.	V	V_{rms} , $T_C = 25\text{ °C}$, $t = 1\text{ min}$

¹⁾ Limited by $T_{J,max}$

²⁾ Pulse width t_{pulse} limited by $T_{J,max}$.

³⁾ The maximum gate-source voltage in the application design should be in accordance to IPC-9592B.

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{th(j-c)}$	-	-	0.98	°C/W	Not subject to production test. Parameter verified by design/characterization according to JESD51-14.
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

3 Operating range

Table 4 Operating range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Recommended turn-on voltage	$V_{GS(on)}$	-	18	-	V	-
Recommended turn-off voltage	$V_{GS(off)}$	-	0	-	V	-

4 Electrical characteristics

at $T_j = 25\text{ °C}$, unless otherwise specified

Table 5 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source voltage	V_{DSS}	650	-	-	V	$V_{GS} = 0\text{ V}$, $I_D = 0.37\text{ mA}$
Gate threshold voltage ¹⁾	$V_{GS(th)}$	3.5	4.5	5.6	V	$V_{DS} = V_{GS}$, $I_D = 3.7\text{ mA}$
Zero gate voltage drain current	I_{DSS}	-	1 3	75 -	μA	$V_{DS} = 650\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 25\text{ °C}$ $V_{DS} = 650\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 175\text{ °C}$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	65 50 46 82	- 62 - -	$\text{m}\Omega$	$V_{GS} = 15\text{ V}$, $I_D = 18.2\text{ A}$, $T_j = 25\text{ °C}$ $V_{GS} = 18\text{ V}$, $I_D = 18.2\text{ A}$, $T_j = 25\text{ °C}$ $V_{GS} = 20\text{ V}$, $I_D = 18.2\text{ A}$, $T_j = 25\text{ °C}$ $V_{GS} = 18\text{ V}$, $I_D = 18.2\text{ A}$, $T_j = 175\text{ °C}$
Internal gate resistance	$R_{G,int}$	-	3.7	-	Ω	$f = 1\text{ MHz}$

¹⁾ Tested after 1 ms pulse at $V_{GS} = +20\text{ V}$. "Linear mode" operation is not recommended. For assessment of potential "linear mode" operation, please contact Infineon sales office.

Table 6 Dynamic characteristics

External parasitic elements (PCB layout) influence switching behavior significantly.
Stray inductances and coupling capacitances must be minimized.

For layout recommendations please use provided application notes or contact Infineon sales office.

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	790	-	pF	$V_{GS} = 0\text{ V}$, $V_{DS} = 400\text{ V}$, $f = 250\text{ kHz}$
Reverse transfer capacitance	C_{rss}	-	4.7	-	pF	$V_{GS} = 0\text{ V}$, $V_{DS} = 400\text{ V}$, $f = 250\text{ kHz}$
Output capacitance ¹⁾	C_{oss}	-	59	77	pF	$V_{GS} = 0\text{ V}$, $V_{DS} = 400\text{ V}$, $f = 250\text{ kHz}$
Output charge ¹⁾	Q_{oss}	-	42	55	nC	calculation based on C_{oss}
Effective output capacitance, energy related ²⁾	$C_{o(er)}$	-	71	-	pF	$V_{GS} = 0\text{ V}$, $V_{DS} = 0...400\text{ V}$
Effective output capacitance, time related ³⁾	$C_{o(tr)}$	-	105	-	pF	$I_D = \text{constant}$, $V_{GS} = 0\text{ V}$, $V_{DS} = 0...400\text{ V}$
Turn-on delay time	$t_{d(on)}$	-	21	-	ns	$V_{DD} = 400\text{ V}$, $V_{GS} = 0/18\text{ V}$, $I_D = 18.2\text{ A}$, $R_{G,ext} = 1.8\ \Omega$; see table 10
Rise time	t_r	-	8.0	-	ns	$V_{DD} = 400\text{ V}$, $V_{GS} = 0/18\text{ V}$, $I_D = 18.2\text{ A}$, $R_{G,ext} = 1.8\ \Omega$; see table 10
Turn-off delay time	$t_{d(off)}$	-	14.0	-	ns	$V_{DD} = 400\text{ V}$, $V_{GS} = 0/18\text{ V}$, $I_D = 18.2\text{ A}$, $R_{G,ext} = 1.8\ \Omega$; see table 10
Fall time	t_f	-	5.0	-	ns	$V_{DD} = 400\text{ V}$, $V_{GS} = 0/18\text{ V}$, $I_D = 18.2\text{ A}$, $R_{G,ext} = 1.8\ \Omega$; see table 10
Turn-ON switching losses ⁴⁾	E_{on}	-	109	-	μJ	$V_{DD} = 400\text{ V}$, $V_{GS} = 0/18\text{ V}$, $I_D = 18.2\text{ A}$, $R_{G,ext} = 1.8\ \Omega$
Turn-OFF switching losses ⁴⁾	E_{off}	-	11	-	μJ	$V_{DD} = 400\text{ V}$, $V_{GS} = 0/18\text{ V}$, $I_D = 18.2\text{ A}$, $R_{G,ext} = 1.8\ \Omega$
Total switching losses ⁴⁾	E_{tot}	-	120	-	μJ	$V_{DD} = 400\text{ V}$, $V_{GS} = 0/18\text{ V}$, $I_D = 18.2\text{ A}$, $R_{G,ext} = 1.8\ \Omega$

Table 7 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Plateau gate to source charge	$Q_{GS(pl)}$	-	5.7	-	nC	$V_{DD} = 400\text{ V}$, $I_D = 18.2\text{ A}$, $V_{GS} = 0\text{ to }18\text{ V}$
Gate to drain charge	Q_{GD}	-	4.2	-	nC	$V_{DD} = 400\text{ V}$, $I_D = 18.2\text{ A}$, $V_{GS} = 0\text{ to }18\text{ V}$
Total gate charge	Q_G	-	22	-	nC	$V_{DD} = 400\text{ V}$, $I_D = 18.2\text{ A}$, $V_{GS} = 0\text{ to }18\text{ V}$

¹⁾ Maximum specification is defined by calculated six sigma upper confidence bound

²⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400 V.

³⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400 V.

⁴⁾ MOSFET used in half-bridge configuration without external diode

Table 8 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source reverse voltage	V_{SD}	-	4.3	-	V	$V_{GS} = 0\text{ V}$, $I_S = 18.2\text{ A}$, $T_j = 25\text{ °C}$
MOSFET forward recovery time	t_{fr}	-	26.8	-	ns	$V_{DD} = 400\text{ V}$, $I_S = 18.2\text{ A}$, $di_S/dt = 1000\text{ A}/\mu\text{s}$; see table 9
MOSFET forward recovery charge ¹⁾	Q_{fr}	-	79	-	nC	$V_{DD} = 400\text{ V}$, $I_S = 18.2\text{ A}$, $di_S/dt = 1000\text{ A}/\mu\text{s}$; see table 9
MOSFET peak forward recovery current	I_{frm}	-	5.9	-	A	$V_{DD} = 400\text{ V}$, $I_S = 18.2\text{ A}$, $di_S/dt = 1000\text{ A}/\mu\text{s}$; see table 9

¹⁾ Q_{fr} includes Q_{oss}

5 Electrical characteristics diagrams

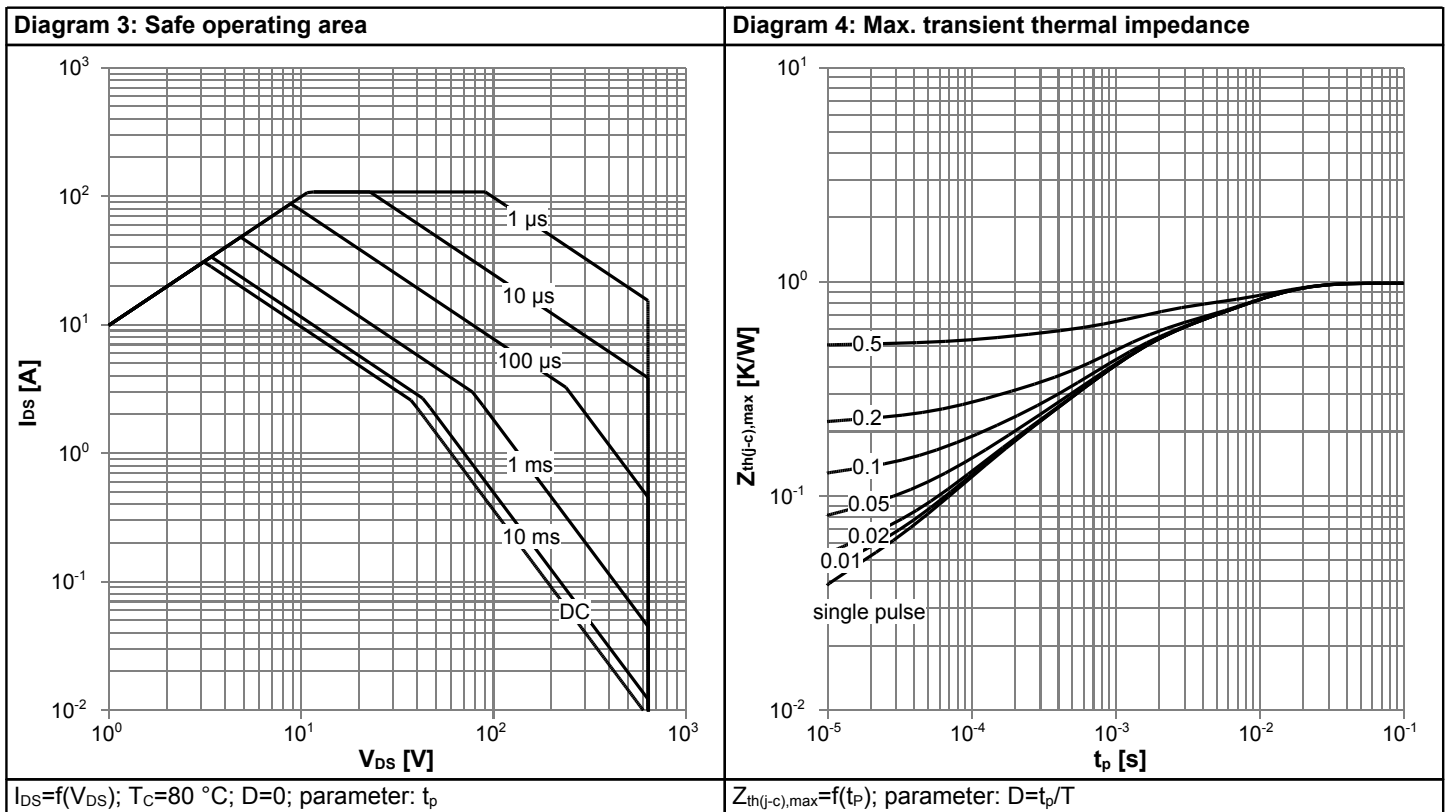
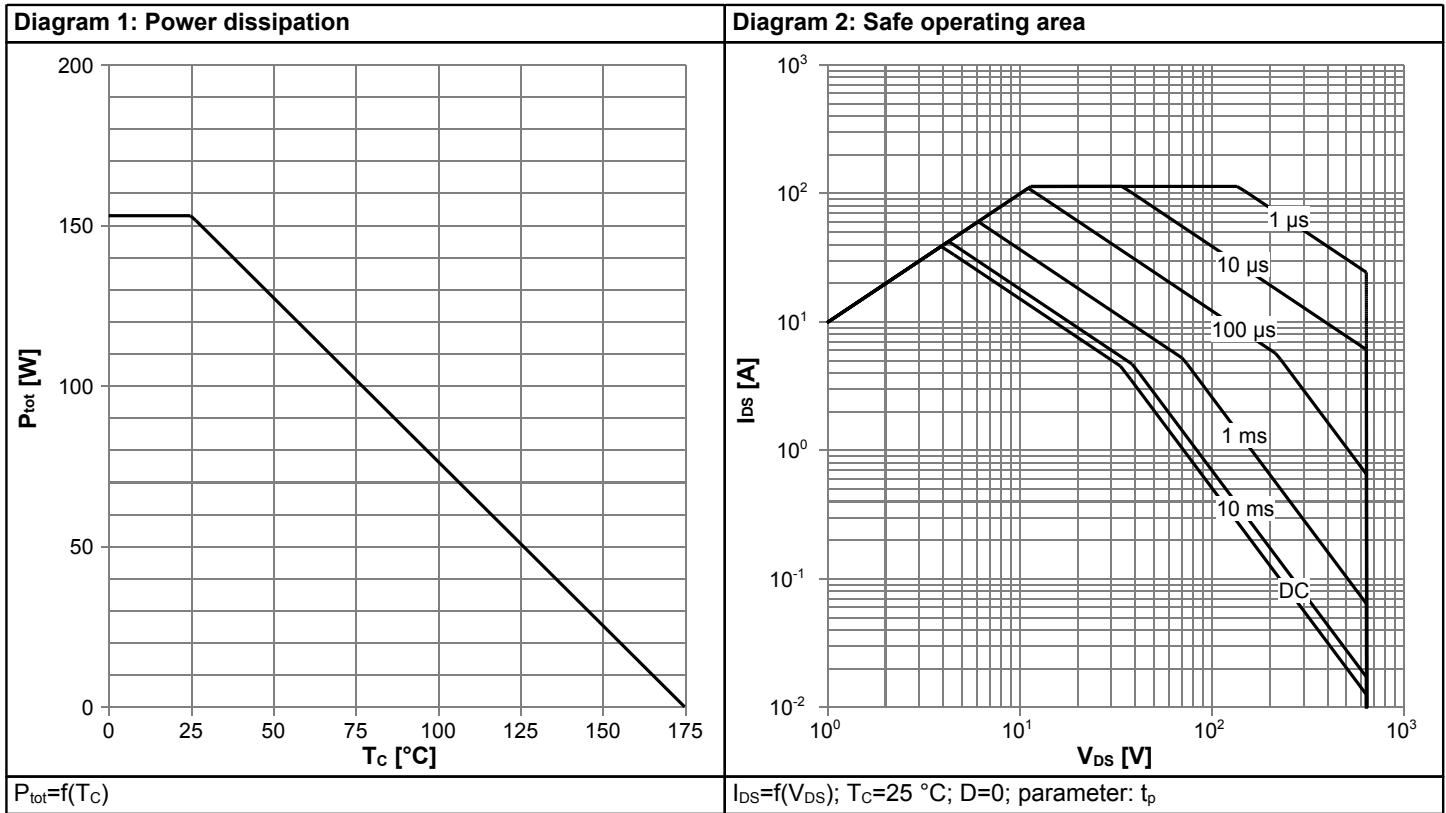
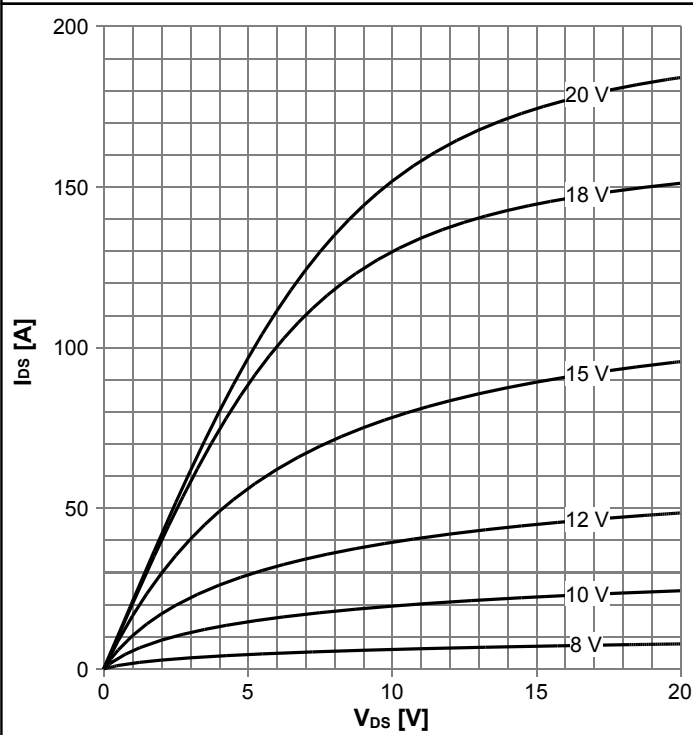
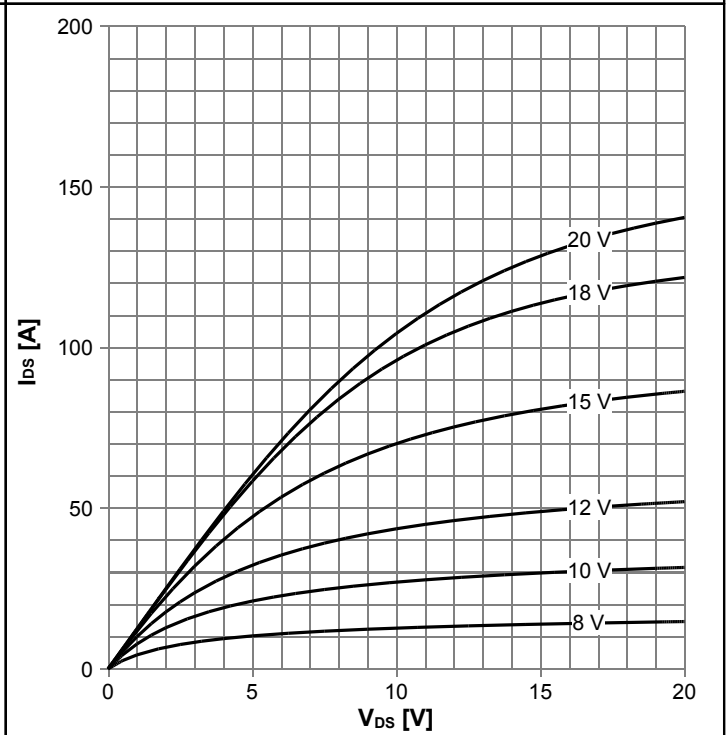


Diagram 5: Typ. output characteristics



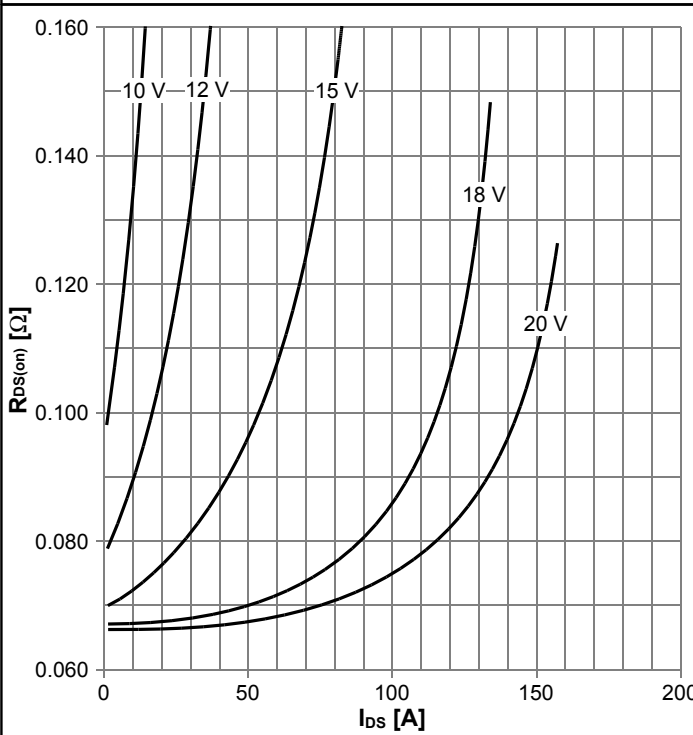
$I_{DS}=f(V_{DS}); T_j=25\text{ °C}; \text{parameter: } V_{GS}$

Diagram 6: Typ. output characteristics



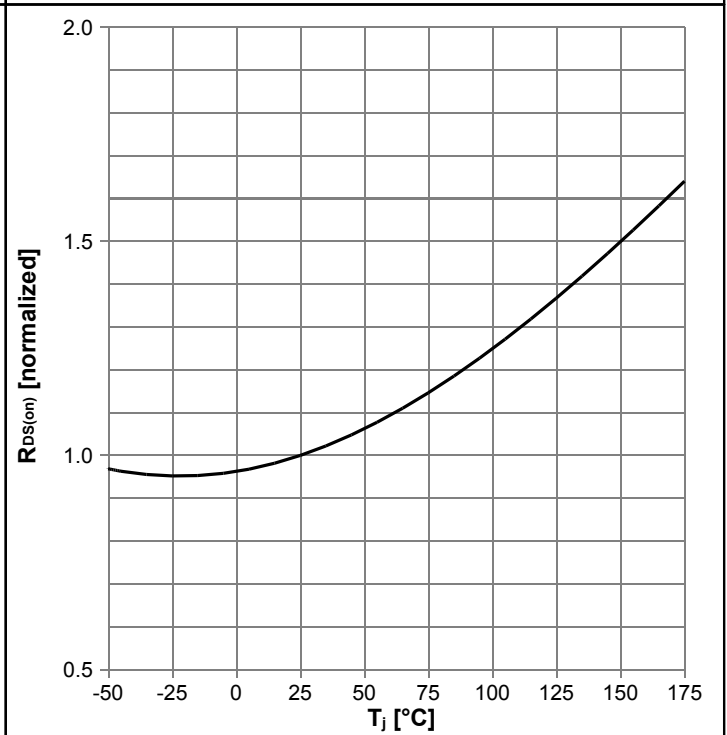
$I_{DS}=f(V_{DS}); T_j=175\text{ °C}; \text{parameter: } V_{GS}$

Diagram 7: Typ. drain-source on-state resistance



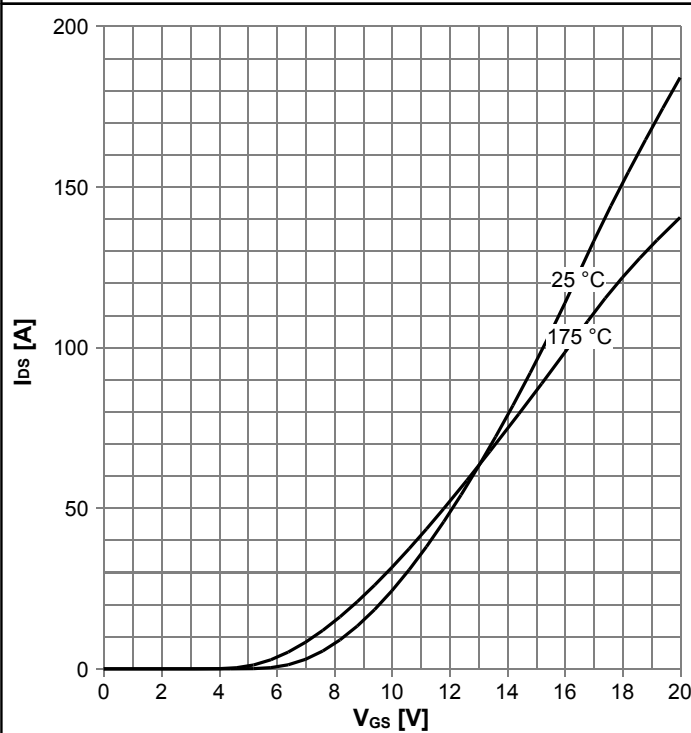
$R_{DS(on)}=f(I_{DS}); T_j=125\text{ °C}; \text{parameter: } V_{GS}$

Diagram 8: Drain-source on-state resistance



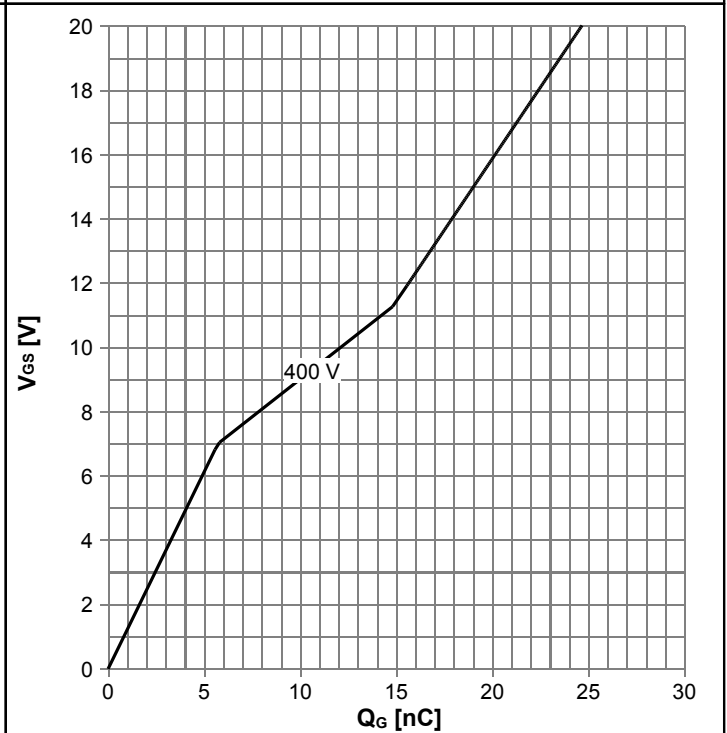
$R_{DS(on)}=f(T_j); I_D=18.2\text{ A}; V_{GS}=18\text{ V}$

Diagram 9: Typ. transfer characteristics



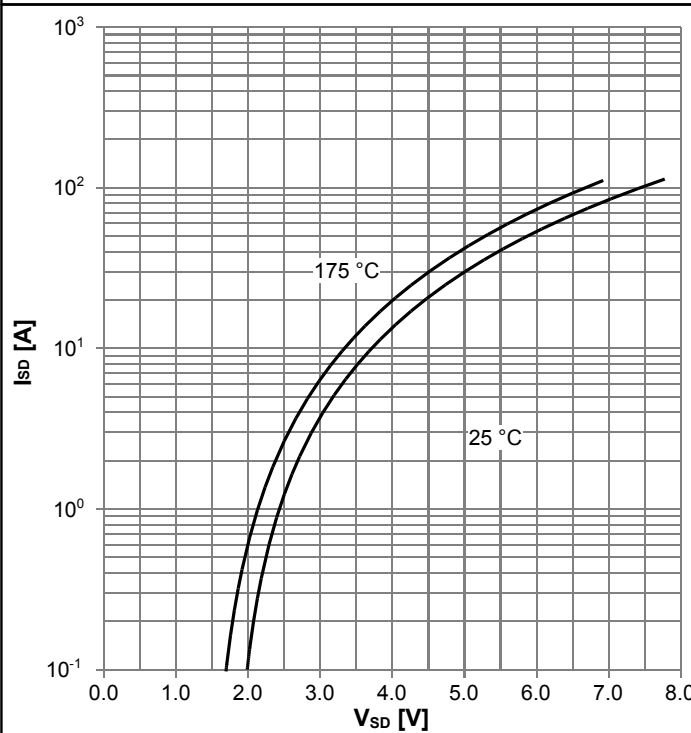
$I_{DS}=f(V_{GS})$; $V_{DS}=20$ V; parameter: T_j

Diagram 10: Typ. gate charge



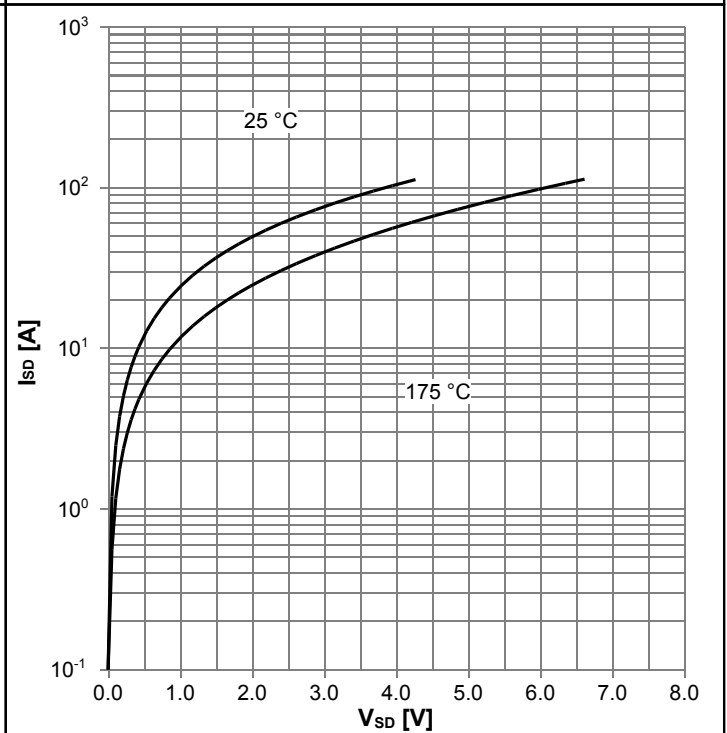
$V_{GS}=f(Q_G)$; $I_D=18.2$ A pulsed; parameter: V_{DD}

Diagram 11: Typ. reverse drain current characteristics



$I_{SD}=f(V_{SD})$; $V_{GS}=0$ V; parameter: T_j

Diagram 12: Typ. reverse drain current characteristics



$I_{SD}=f(V_{SD})$; $V_{GS}=18$ V; parameter: T_j

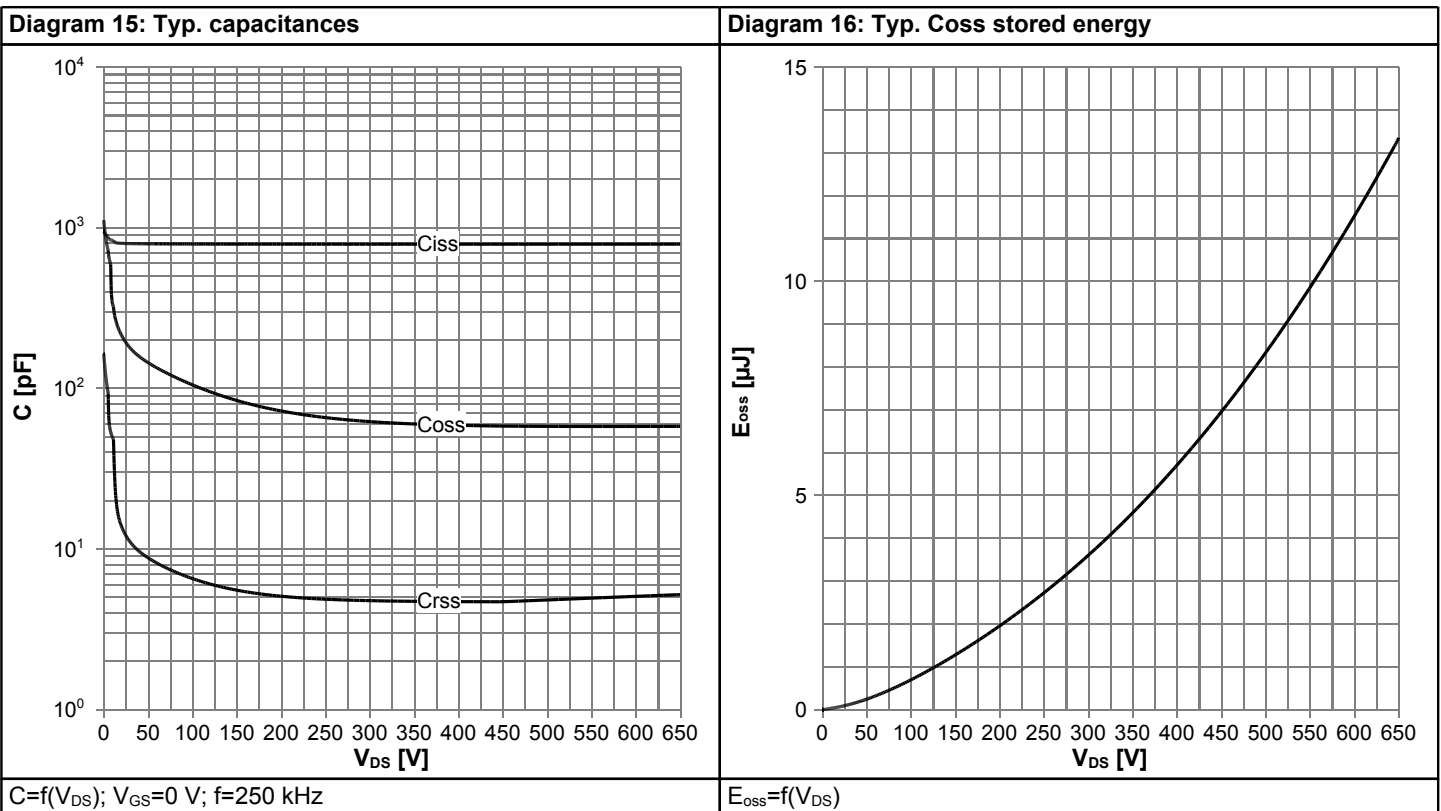
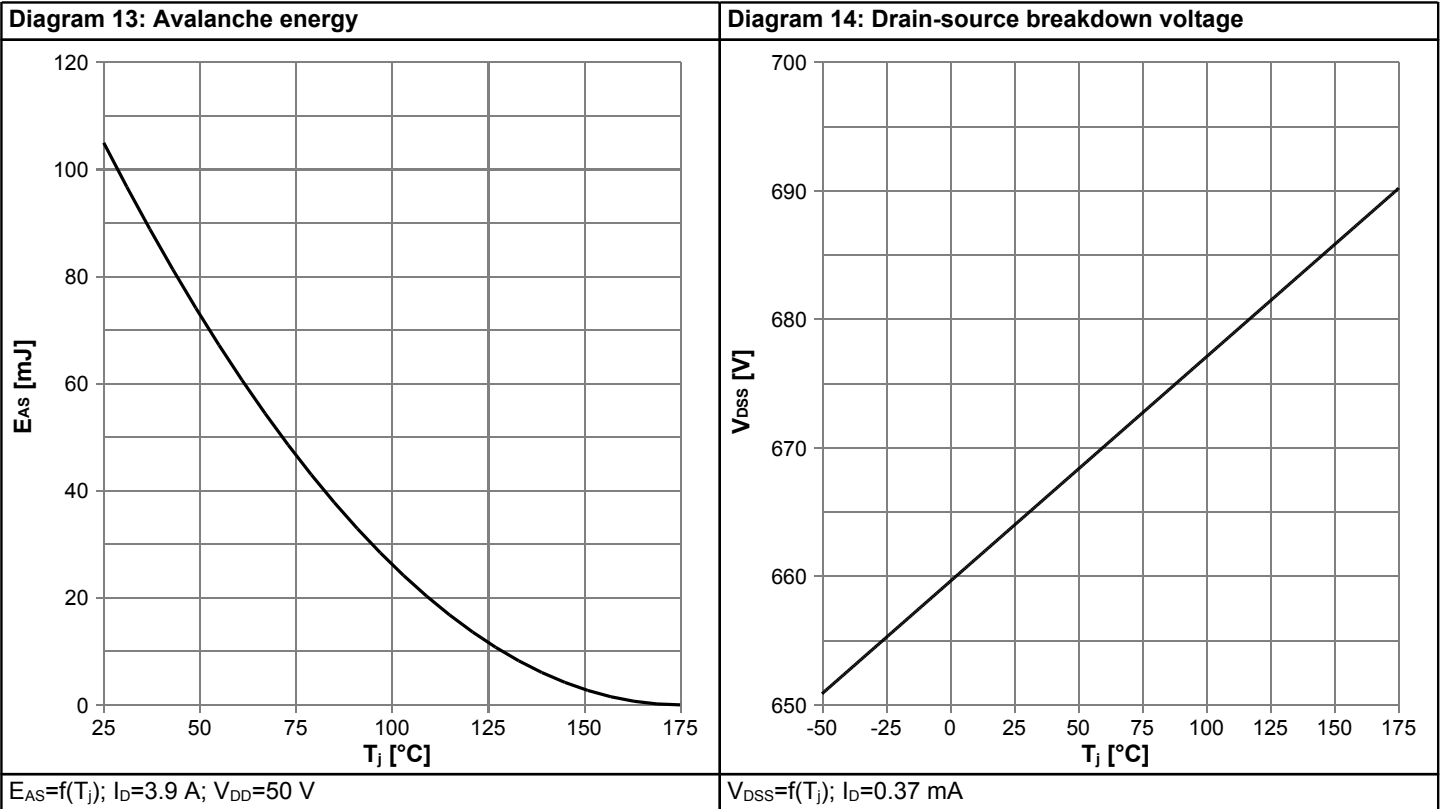
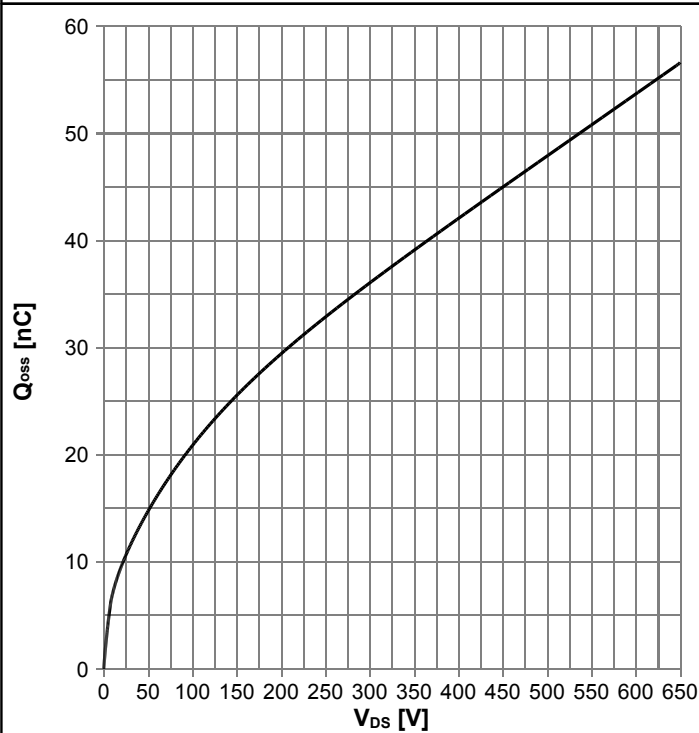
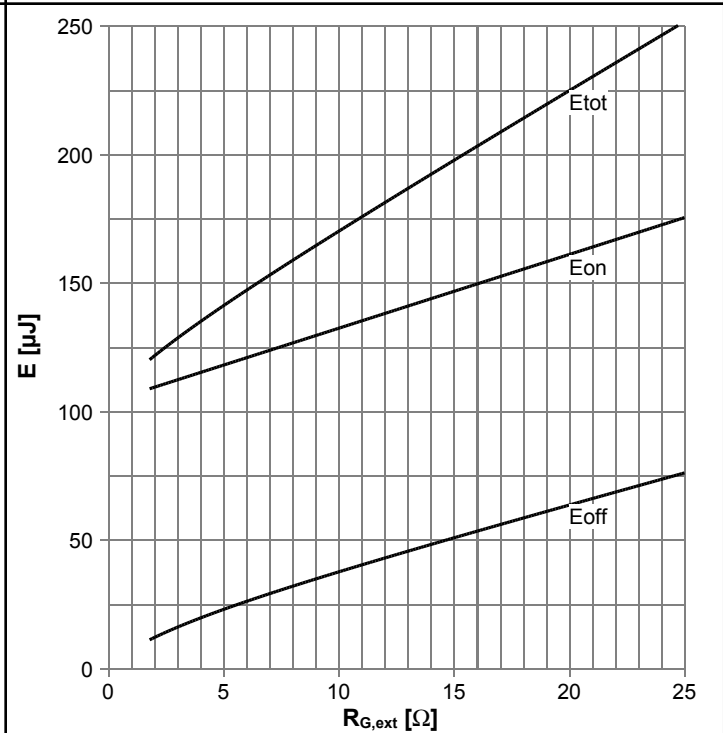


Diagram 17: Typ. Q_{oss} output charge



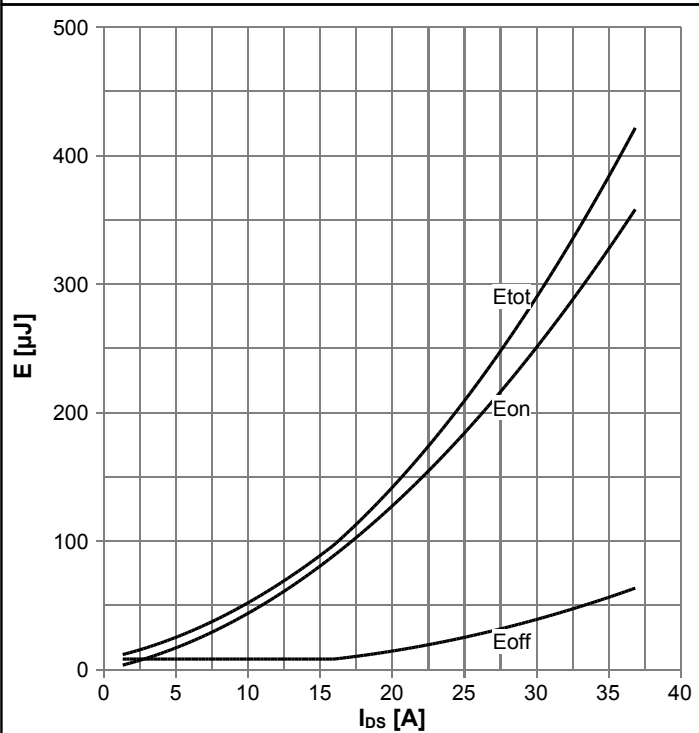
$Q_{oss}=f(V_{DS})$

Diagram 18: Typ. Switching Losses vs R_{G,ext}



$E=f(R_{G,ext}); V_{DD}=400\text{ V}; V_{GS}=0/18\text{ V}; I_D=18.2\text{ A}$

Diagram 19: Typ. Switching Losses vs switching current



$E=f(I_{DS}); V_{DD}=400\text{ V}; V_{GS}=0/18\text{ V}; R_{G,ext}=1.8\ \Omega$

6 Test Circuits

Table 9 Body diode characteristics

Test circuit for body diode characteristics	Body diode recovery waveform

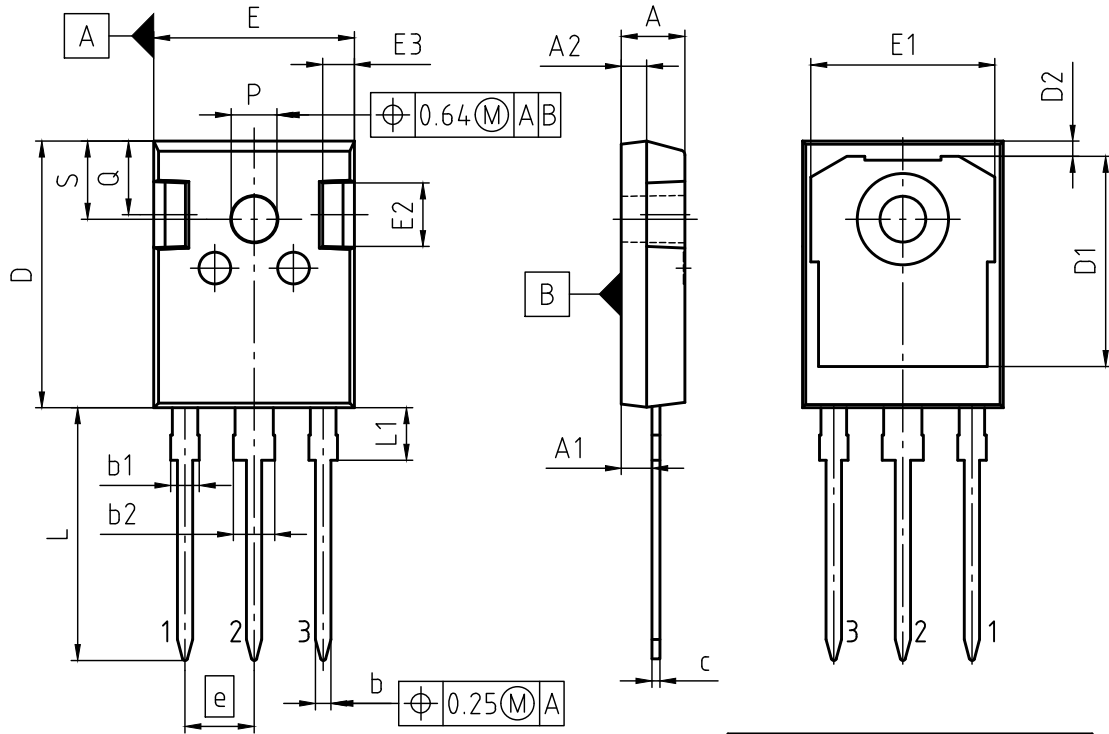
Table 10 Switching times

Switching times test circuit for inductive load	Switching times waveform

Table 11 Unclamped inductive load

Unclamped inductive load test circuit	Unclamped inductive waveform

7 Package Outlines



PACKAGE - GROUP NUMBER: PG-TO247-3-U06		
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	4.83	5.21
A1	2.27	2.54
A2	1.85	2.16
b	1.07	1.33
b1	1.90	2.41
b2	2.87	3.38
c	0.55	0.68
D	20.80	21.10
D1	16.25	17.65
D2	0.95	1.35
E	15.70	16.13
E1	13.10	14.15
E2	3.68	5.10
E3	1.00	2.60
e	5.44	
N	3	
L	19.80	20.32
L1	4.10	4.47
øP	3.50	3.70
Q	5.49	6.00
S	6.04	6.30

NOTE:
DIMENSIONS DO NOT INCLUDE MOLDFLASH; PROTRUSION OR GATE BURRS

Figure 1 Outline PG-TO247-3, dimensions in mm

8 Appendix A

Table 12 Related Links

- IFX CoolSiC CoolSiC™ MOSFET 650 V G2 Webpage: www.infineon.com
- IFX CoolSiC CoolSiC™ MOSFET 650 V G2 application note: www.infineon.com
- IFX CoolSiC CoolSiC™ MOSFET 650 V G2 simulation model: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IMW65R050M2H

Revision: 2024-03-05, Rev. 2.2

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2023-11-02	Release of final version
2.1	2024-02-29	updated simulation model; included Eon and Eoff data and diagrams
2.2	2024-03-05	minor layout changes

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